

POLYCIDE GATE STRUCTURE AND MANUFACURING METHOD  
THEREOF

ABSTRACT OF THE DISCLOSURE

A polycide gate structure and the manufacturing method thereof are provided. The manufacturing method includes the following steps of: (a) providing a substrate; (b) forming a polysilicon layer and a silicide layer upon the substrate separately; (c) removing a part of the silicide layer for defining a silicide structure having a side wall; (d) forming a protecting structure covering the side wall of the silicide structure; (e) removing the polysilicon layer not covered by the silicide structure and the protecting structure for obtaining a polysilicon structure having laterals; and (f) oxidating the polysilicon structure for forming an insulating structure on laterals of the polysilicon structure.